L Number	Hits	Search Text	DB	Time stamp
1	1083	(rh with ir) and (electrode adj (layer or	USPAT;	2004/10/31 09:31
		film))	US-PGPUB;	
			EPO; JPO;	
	,		DERWENT;	
_	0.7	/	IBM_TDB	2004/10/21 00:20
2	97	(rh with ir) with (electrode adj (layer or film))	USPAT; US-PGPUB;	2004/10/31 09:39
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	4	(rh with ir) with (electrode adj (layer or	USPAT;	2004/10/31 09:44
İ		film)) with laminat\$	US-PGPUB;	
			EPO; JPO;	,
			DERWENT;	
4			IBM_TDB	2004/10/21 00:45
4	2	(rhodium with iridium) with (electrode adj (layer or film)) with laminat\$	USPAT; US-PGPUB;	2004/10/31 09:45
		(tayer or firm)) with familiats	EPO; JPO;	
			DERWENT;	
			IBM TDB	
5	10	(rhodium with iridium) with (electrode)	USPAT;	2004/10/31 09:51
		with laminat\$	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	2004/10/21 10 10
6	26	(rh with ir) with (electrode) with laminat\$	USPAT;	2004/10/31 10:18
		Tamiliaca	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
7	77	((rh or rhodium) with (ir or iridium))	USPAT;	2004/10/31 10:20
		with (condutor or metal) with laminat\$	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
8	.1	/in an inidium\ add laminate add /uh au	IBM_TDB	22004/10/21 10-01
-	· - · -	(ir or iridium) adj laminat\$ adj (rh or rhodium)	USPAT; US-PGPUB;	2004/10/31 10:21
		inoutum	EPO; JPO;	
			DERWENT;	
			IBM TDB	
9	195	,	USPĀT;	2004/10/31 10:22
		rhodium)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
10	35	(ir or iridium) with laminat\$ with (rh or	IBM_TDB USPAT;	2004/10/31 10:56
	33	rhodium) with electrode	US-PGPUB;	
			EPO; JPO;	
	1	, ·	DERWENT;	
			IBM_TDB	
11	167	thickness with (rh or rhodium) with	USPAT;	2004/10/31 10:56
	1	electrode	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT; IBM TDB	
12		(thickness adj (rh or rhodium)) with (ir	USPAT;	2004/10/31 10:57
		or iridium) with electrode	US-PGPUB;	-001, 10, 01 10.07
			EPO; JPO;	
			DERWENT;	
		l	IBM_TDB	
13	3	(thickness adj (rh or rhodium)) with	USPAT;	2004/10/31 11:45
		electrode	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
14	0	(ir or iridium) with (rh or rhodium) with	USPAT;	2004/10/31 11:47
		(electrode adj annealed)	US-PGPUB;	
		· ·	EPO; JPO;	
:			DERWENT;	
		•	IBM_TDB	

15	0	(ir or iridium) with (rh or rhodium) with	USPAT;	2004/10/31 11:47
		(electrode adj anneal\$)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	1
16	8	(ir or iridium) with (rh or rhodium) with	USPAT;	2004/10/31 11:51
		electrode with anneal\$	US-PGPUB;	
			EPO; JPO;	
;	1		DERWENT;	
4.5			IBM_TDB	
17	57	((= = = = = = = = , = = = = = = = = =	USPĀT;	2004/10/31 12:13
		electrode) same anneal\$	US-PGPUB; EPO; JPO;	
	:		DERWENT;	
			IBM TDB	
18	26	(((ir or iridium) adj (rh or rhodium))	USPAT;	2004/10/31 13:25
		with electrode) same anneal\$	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
19	497	257/13.ccls.	IBM_TDB USPAT;	2004/10/31 14:14
	457	237/13.0013.	US-PGPUB;	2004/10/31 14:14
	[i		EPO; JPO;	
			DERWENT;	
			IBM TDB	
20	1072	257/79.ccls.	USPAT;	2004/10/31 14:15
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
21	597	257/80.ccls.	USPAT;	2004/10/31 14:16
			US-PGPUB;	2001, 20, 02 21120
			EPO; JPO;	
		·	DERWENT;	
00	050	057/04	IBM_TDB	0004/10/01 14 16
22	953	257/94.ccls.	USPAT; US-PGPUB;	2004/10/31 14:16
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
23	695	257/184.ccls.	USPAT;	2004/10/31 14:17
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
24	1304	257/431.ccls.	USPAT;	2004/10/31 14:17
- -			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
25		057/420 1	IBM_TDB	0004/10/01
25	1270	257/432.ccls.	USPAT;	2004/10/31 14:18
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
26	266	257/86.ccls.	USPAT;	2004/10/31 14:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
27	1596	257/103.ccls.	IBM_TDB USPAT;	2004/10/31 14:18
		20., 200.0010.	US-PGPUB;	5004/10/2T T4:T0
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
28	550	257/436.ccls.	USPAT;	2004/10/31 14:20
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
	l.			L

29	3	257/13.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; 2004/10/31 14:1 US-PGPUB; EPO; JPO; DERWENT;	4
			IBM TDB	
30	19	257/79.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; 2004/10/31 14:1 US-PGPUB; EPO; JPO; DERWENT;	5
31	. 5	257/80.ccls. and ((rh or rhodium) with (ir or iridium))	IBM_TDB USPAT; 2004/10/31 14:1 US-PGPUB; EPO; JPO;	6
32	11	257/94.ccls. and ((rh or rhodium) with (ir or iridium))	DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO;	6
33	2	257/184.ccls. and ((rh or rhodium) with (ir or iridium))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT.	7
34	8	257/431.ccls. and ((rh or rhodium) with (ir or iridium))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; 2004/10/31 14:1	7
35	4	257/432.ccls. and ((rh or rhodium) with (ir or iridium))	IBM_TDB USPAT; 2004/10/31 14:1 US-PGPUB; EPO; JPO; DERWENT;	8
36	1	257/86.ccls. and ((rh or rhodium) with (ir or iridium))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; 2004/10/31 14:1	8
37	43	257/103.ccls. and ((rh or rhodium) with (ir or iridium))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; 2004/10/31 14:1	8
38	3	257/436.ccls. and ((rh or rhodium) with (ir or iridium))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; 2004/10/31 14:2	0
40	616	257/\$.ccls. and ((rh or rhodium) with (ir or iridium) with electrode)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; 2004/10/31 14:2	1
41	100	257/\$.ccls. and ((rh or rhodium) with (ir or iridium) with electrode with nitride)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; 2004/10/31 14:2	8
42	22	. 257/\$.ccls. and ((rh or rhodium) with (ir or iridium) with electrode with nitride) and light	IBM_TDB USPAT; 2004/10/31 14:2 US-PGPUB; EPO; JPO;	8
-	16	(nitride adj semiconductor) and (electrode with rhodium with iridium)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	7

	,			
-	0	sonobe.inv	USPAT;	2004/10/16 12:28
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	sonobe.inv. and (electrode with rhodium	USPAT;	2004/10/16 12:34
	*	with iridium)	US-PGPUB;	2001,10,10 12.01
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	sonobe.inv. and (electrode with rh with	USPAT;	2004/10/16 12:29
		ir)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	2004/10/20 17:42
_	1	sonobe.inv. and (rh with ir) and (nitride	USPAT;	2004/10/29 17:43
		adj semiconductor)	US-PGPUB; EPO; JPO;	İ
			DERWENT;	
			IBM TDB	•
_	16	 sonobe.inv. and (nitride adj	USPAT;	2004/10/16 12:31
1	1	semiconductor)	US-PGPUB;	
		<i>'</i>	EPO; JPO;	
1	•		DERWENT;	
		·	IBM_TDB	
-	2		USPĀT;	2004/10/16 12:32
	ĺ	semiconductor) and rhodium	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/10/16 10 22
-	3		USPAT;	2004/10/16 12:33
		semiconductor) and rh	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	sonobe.inv. and (nitride adj	USPAT;	2004/10/16 12:33
		semiconductor) and iridium	US-PGPUB;	2001, 20, 20 22,00
			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
-	1		USPAT;	2004/10/16 12:33
		semiconductor) and ir	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	2	sonobe.inv. and (rhodium with iridium)	IBM_TDB USPAT;	2004/10/16 12:34
-	2	Sonobe.inv. and (inoutum with illulum)	US-PGPUB;	2004/10/10 12:34
			EPO; JPO;	
			DERWENT;	.
			IBM TDB	
- '	1136	(rh with ir) with electrode	USPAT;	2004/10/29 20:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	495	((rh with ir) with electrode) and nitride	USPAT;	2004/10/29 23:32
			US-PGPUB;	·
			EPO; JPO; DERWENT;	
	İ		IBM TDB	
_	۵	((rh with ir) with (p adj electrode)) and	USPAT;	2004/10/29 19:07
]	nitride	US-PGPUB;	2004, 10, 25 19.01
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	5	((rh with ir) with (p adj side adj	USPAT;	2004/10/29 20:08
		electrode)) and nitride	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
L	L	<u></u>	IBM_TDB	

-	0	20030209717.pn. and (temperature or	USPAT;	2004/10/29 20:08
		anneal)	US-PGPUB;	
			EPO; JPO;	1
			DERWENT; IBM TDB	
l _	1	20030209717.pn. and (temperature or	USPAT;	2004/10/29 21:42
	_	anneal\$)	US-PGPUB;	2004/10/23 21:42
		dimedity)	EPO; JPO;	
			DERWENT;	
İ			IBM TDB	
-	199	((rh with ir) with electrode) and laminat\$	USPAT;	2004/10/29 20:13
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
- 4	26	((rh with ir) with electrode) with	USPAT;	2004/10/29 20:20
		laminat\$	US-PGPUB;	
			EPO; JPO;	·
			DERWENT;	1
l _	1	((rh with ir) with (laminat\$ adj	IBM_TDB USPAT;	2004/10/29 20:22
] _	1	((In with II) with (laminat; ad)	US-PGPUB;	2004/10/29 20:22
		electiode//	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	((rhodium with iridium) with (laminat\$ adj	USPAT;	2004/10/29 20:23
1		electrode))	US-PGPUB;	
		,	EPO; JPO;	
,			DERWENT;	
			IBM TDB	
-	0	((rhodium with iridium) with (two adj	USPAT;	2004/10/29 20:23
		layer adj electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
]			IBM_TDB	0004/20/00 00 04
-	0	(((((USPAT;	2004/10/29 20:24
	-	layer adj electrode))	US-PGPUB; EPO; JPO;	
:		·	DERWENT;	
			IBM TDB	
_	6	((rhodium with iridium) and (two adj layer	USPAT;	2004/10/29 20:25
		adj electrode))	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
1			IBM_TDB	
-	0	1 , ,	USPAT;	2004/10/29 20:25
		layer adj electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	8	((rhodium with iridium) and (double adj	IBM_TDB USPAT;	2004/10/29 20:28
	·	((Inodium with Iridium) and (double adj layer adj electrode))	US-PGPUB;	2004/10/23 20:28
		layer day electrode//	EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
-	8	((rhodium with iridium) and (multiple adj	USPAT;	2004/10/29 20:30
	[layer adj electrode))	US-PGPUB;	· · · · · · · · · · · · · · · · · · ·
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	13	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/10/29 20:35
		layer adj electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
<u>_</u>	183	 ((rhodium with iridium) and (plurality adj	IBM_TDB USPAT;	2004/10/29 20:35
	103	electrode))	USPAT; US-PGPUB;	2004/10/23 20:35
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
				

adj electrode)					
Company Comp	-	2	((rhodium with iridium) with (plurality	USPAT;	2004/10/29 20:36
- 0 ((rhodium with iridium) with (multiple ad) USPAT; USPAT			adj electrode))		
IMM TOB		•			
- 0					
	_	_	//whodium with imidium) with /multiple adi		2004/10/29 20.37
-		0			2004/10/29 20:37
-			electiode//		
-					1
-				1	1
	_	2	((rhodium with iridium) with (multi adj		2004/10/29 20:37
- 0				1	
- 0				EPO; JPO;	
- 0			,	DERWENT;	
electrode)					
- 0 ((rhodium with iridium) with (dual adj DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPA	-	0		1	2004/10/29 20:37
Company Comp			electrode))	1	
- 0				I .	
- 0 ((rhodium with iridium) with (dual adj USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PCPUB; EPO; JPO; DERWENT; US-PCPUB; EPO; JPO; DERWENT; US				1	
		_	(/mhodinm vith imidium) vith /duol odi		2004/10/20 20:30
- 0	-	U			2004/10/29 20:38
Company Comp			erectione, i	1	
Company Comp					
- 0	1				
electrode)	-	0	((rhodium with iridium) with (double adi		2004/10/29 20:38
- 4 ((rhodium with iridium) with (two adj electrode))	1	_			
- 4				EPO; JPO;	
- 4 ((rhodium with iridium) with (two adj electrode)) - 10 ((rhodium with iridium) with (laminat\$ EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; D				DERWENT;	
electrode)			•	_	
Company Comp	-	4		1	2004/10/29 20:40
DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT;			electrode))		
TBM_TDB					
10					
With electrode)	_	1.0	//rhodium with iridium) with /laminats		2004/10/29 20:45
Comparison of the content of the c		10			2004/10/29 20:45
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB			with electione,		
- 26 ((rh with ir) with (laminat\$ with electrode)) - 169 laminat\$ with ir with rh - 26 laminat\$ with ir with rh with electrode - 26 laminat\$ with ir with rh with electrode - 10 laminat\$ with iridium with rhodium with electrode - 8 (laminat\$ with (ir adj rh)) with electrode - 8 (laminat\$ with iridium the electrode 18					
electrode)				1	
Top	[-	26	((rh with ir) with (laminat\$ with	USPĀT;	2004/10/29 21:17
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			electrode))	US-PGPUB;	
TBM_TDB					
- 169 laminat\$ with ir with rh - 26 laminat\$ with ir with rh with electrode - 26 laminat\$ with ir with rh with electrode - 10 laminat\$ with iridium with rhodium with electrode - 8 (laminat\$ with (ir adj rh)) with electrode 10 10 10 10 10 10 10 1					
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			l aminano de la la la la la la la la la la la la la	_	0004/10/00 == ==
- 26 laminat\$ with ir with rh with electrode USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	-	169	laminats with ir with rh	ì	2004/10/29 21:03
- 26 laminat\$ with ir with rh with electrode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 10 laminat\$ with iridium with rhodium with electrode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 8 (laminat\$ with (ir adj rh)) with electrode USPAT; USPAUB; EPO; JPO; DERWENT; IBM_TDB	ļ				
laminat\$ with ir with rh with electrode IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; electrode IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB					
- 26 laminat\$ with ir with rh with electrode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; electrode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB				-	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	-	26	laminat\$ with ir with rh with electrode		2004/10/29 21:03
The second of th			,		
- 10 laminat\$ with iridium with rhodium with electrode					
- 10 laminat\$ with iridium with rhodium with electrode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB				DERWENT;	
electrode B (laminat\$ with (ir adj rh)) with electrode (laminat\$ with (ir adj rh)) with electrode B (laminat\$ with (ir adj rh)) with electrode US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	-	. 10	·		2004/10/29 21:07
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT; IBM_TDB DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT; IBM_TDB DERWENT; IBM_TDB			electrode	· · · · · · · · · · · · · · · · · · ·	
- 8 (laminat\$ with (ir adj rh)) with electrode IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
- 8 (laminat\$ with (ir adj rh)) with electrode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	_	0	/lominaté with /in adi whll with alastuada		2004/10/20 21:00
EPO; JPO; DERWENT; IBM_TDB		o	(raminate with (ii ad) in)) with electrode	· ·	2004/10/23 21:09
DERWENT; IBM_TDB					
IBM_TDB					
	-	2	ir adj rh adj electrode	USPAT;	2004/10/29 21:12
US-PGPUB;		·			
EPO; JPO;					
DERWENT;					
IBM TDB	1 1			IBM TDB	

	-	0	iriudium adj rhodium adj electrode		2004/10/29 21:11
		j			
1					
1 iridium adj rhodium adj electrode				· ·	
EPO; JPO; DERMENT; IBM TOB USPAT; US-COUB; ENOUTH TOB USPAT; USPAT; US-COUB; ENOUTH TOB USPAT; US-COUB; ENOUTH TOB USPAT; US-CO	-	1	iridium adj rhodium adj electrode		2004/10/29 21:11
DERMENT: IBM TOB USFAT:		ļ		US-PGPUB;	
1					
- 0 iridium adj rhodium adj terminal USPĀT; US-PGPUB; EPO; JPO; DERMENT; IBM TDB USPĀT; US-EGFUB; EPO; JPO; JPO; DERMENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J				-	
US-PGPUB; POP; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB USEAT; US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J			inidium adi ubadium adi tauminal		2004/10/20 21.11
- 0 ir adj rh adj terminal	-	١	iridium adj rhodium adj terminal		2004/10/29 21:11
- 0 ir adj rh adj terminal DERWENT; IBM TOB USFĀT; US-PGPUB; EPG, JPG; DERWENT; IBM TOB USFĀT; US-PGPUB; EPG,					
Tem TDB USPAT; US-PCPUB; EEPO; JPO; DERWENT; IEM TDB USPAT; US-PCP					
- 0 (ir adj rh adj terminal USPAT; USPAT; USPAT; USPACHUR; IBM TDB USPAT; USPERURN; IBM TDB USPAT;					•
- 10	-	0	ir adj rh adj terminal		2004/10/29 21:12
Company Comp				US-PGPUB;	
two adj layered) with (ir or iridium) USPAT: USP-GPUB; EPO; JPO; DERWENT; IBM TDB USPAT: USP-GPUB; EPO; JPO; D					
10					
With (rh or rhodium)		10	(h., add]	_	2004/10/20 21:12
- 93 (nitride adj semiconductor) with (laminats) with electrode) - 1 (nitride adj semiconductor) with (laminats) with electrode) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) and (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or refPUB; EPO, JPO; DERWENT; IEM TDB USPAT; US-PEPUB; EPO, JPO; DERWENT; IEM TDB USPAT; USPA	_	10	, (,,, (,		2004/10/29 21:13
- 93 (nitride adj semiconductor) with (laminats with electrode) - 1 (nitride adj semiconductor) with (laminats with electrode) - 1 (nitride adj semiconductor) with (laminats with electrode) with (ir or iridium) with (sp. 2004/10/29 21:19 - 1 (nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers)			with (in or inoutum)		
- 93 (nitride adj semiconductor) with (laminats with electrode) - 1 (nitride adj semiconductor) with (laminats with electrode) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers)					
- 93 (nitride adj semiconductor) with (laminats with electrode) - 1 (nitride adj semiconductor) with (laminats EPGUB; EPG, JPG)				-	
with electrode)	-	93	(nitride adj semiconductor) with (laminat\$		2004/10/29 21:18
- 1 (nitride adj semiconductor) with (laminats with electrode) with (ir or iridium) with (pro rhodium) (intride adj semiconductor) with (two adj layered) with (ir or iridium) with (pro rhodium) (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (pro rhodium) (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (pro permenn; IBM TDB (pro permenn) (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (pro permenn) (p					
- 1 (nitride adj semiconductor) with (laminats with electrode) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers)	,				
- 1 (nitride adj semiconductor) with (laminats with electrode) with (ir or iridium) with (provided provided pro				· ·	
with electrode) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers)		,	(mituida adi ami andustau)		2004/10/20 21-10
(rh or rhodium) (rh or rhodium) (nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) (nitride adj semiconductor) and (ir adj rh adj double adj layers) (nitride adj semiconductor) and (ir adj rh adj double adj layers) (nitride adj semiconductor) and (ir adj rh adj double adj layers) (nitride adj semiconductor) and (ir adj rh adj double adj layers) (nitride adj semiconductor) and (ir adj rh adj double adj layers)	-	1			2004/10/29 21:19
- 0 (nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers)					
- 0 (nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 1 (nitride adj semiconductor) and (ir adj layers) and ((ir or iridium) with (rh or rhodium)) - 1 (nitride adj semiconductor) and (ir adj layers); layers); layers (layers); layers (layers); layers (layers); layers (layers); layers); layers (layers); lay			(III of Inoctum)		
layered) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (double adj layers) and ((ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (ir adj rh adj double adj layers) O (nitride adj semiconductor) and (ir adj rh adj double adj layers) O (nitride adj semiconductor) and (ir adj rh adj double adj layers) O (nitride adj semiconductor) and (ir adj rh adj double adj layers)				•	
rhodium) (nitride adj semiconductor) with (dual adj Layered) with (ir or iridium) with (rh or rhodium) 1 (nitride adj semiconductor) with (two adj Layers) with (ir or iridium) with (rh or rhodium) 1 (nitride adj semiconductor) with (two adj Layers) with (ir or iridium) with (rh or rhodium) 2 (nitride adj semiconductor) with (dual adj Layers) with (ir or iridium) with (rh or rhodium) 2 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) 3 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) 4 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) 5 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) 6 (nitride adj semiconductor) and (ir adj rh adj double adj layers) 7 (nitride adj semiconductor) and (ir adj rh adj double adj layers) 8 (nitride adj semiconductor) and (ir adj rh adj double adj layers) 9 (nitride adj semiconductor) and (ir adj rh adj double adj layers) 10 (nitride adj semiconductor) and (ir adj rh adj double adj layers) 11 (nitride adj semiconductor) and (ir adj rh adj double adj layers) 12 (004/10/29 21:20 004/10/29 2	_	0	(nitride adj semiconductor) with (two adj	USPĀT;	2004/10/29 21:19
- 0 (nitride adj semiconductor) with (dual adj USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;				US-PGPUB;	
TBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT;			rhodium)		
- 0 (nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium) - 1 (nitride adj semiconductor) with (two adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (dual adj layers) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layers) with (ir or iridium) with (rh or rhodium) - 4 (nitride adj semiconductor) with (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (double adj layers) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layers)			,		
layered) with (ir or iridium) with (rh or rhodium) 1 (nitride adj semiconductor) with (two adj layer\$) with (ir or iridium) with (rh or rhodium) 1 (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) 2004/10/29 21:20 2004/10/29 21:31 2004/10/29 21:31 2004/10/29 21:31 2004/10/29 21:31 2004/10/29 21:31 2004/10/29 21:31 2004/10/29 21:31	_	0	(nitride adi semiconductor) with (dual adi		2004/10/29 21:19
rhodium) (nitride adj semiconductor) with (two adj layer\$) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$)				1	2004/10/25 21.15
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
1 (nitride adj semiconductor) with (two adj layer\$) with (ir or iridium) with (rh or rhodium) 0 (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) 0 (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) 0 (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) 1 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) 1 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) 2 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) 1 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) 2 (004/10/29 21:20 (004/10/29 21:20 (004/10/29 21:21 (004/10/29 21:21 (004/10/29 21:21 (004/10/29 21:21 (004/10/29 21:31					
layer\$) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$)				_	
rhodium) (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or hodium)) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$)	-	1			2004/10/29 21:20
- 0 (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) - 4 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$)	†				
- 0 (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) - 0 (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) - 4 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$)			THOUTUM)	l .	
O (nitride adj semiconductor) with (dual adj layer\$) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or adj layer\$) with (ir or iridium) with (rh or hodium) O (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) DERWENT; SOU4/10/29 21:20 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
layer\$) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) O (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) DERWENT; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	0	(nitride adj semiconductor) with (dual adj		2004/10/29 21:20
rhodium) Comparison of the proof of the pro]			
- 0 (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) - 4 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 1 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 1 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 1 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 2004/10/29 21:21 - 2004/10/29 21:31 - 2004/10/29 21:31					
- 0 (nitride adj semiconductor) with (double adj layer\$) with (ir or iridium) with (rh or rhodium) - 4 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 1 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 1 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 2004/10/29 21:21 - 2004/10/29 21:21 - 2004/10/29 21:31 - 2004/10/29 21:31					
adj layer\$) with (ir or iridium) with (rh or rhodium) - 4 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$)]	_	(nitual do note and another and a transfer of the state o		0004/10/00 01 01
or rhodium) (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	-	١		· ·	2004/10/29 21:21
The adj double adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 4 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) - 0 (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) 1BM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;			01 2.10d1diii)	1	
4 (nitride adj semiconductor) and (double adj layer\$) and ((ir or iridium) with (rh or rhodium)) O (nitride adj semiconductor) and (ir adj rh adj double adj layer\$) USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;]
or rhodium)) - 0 (nitride adj semiconductor) and (ir adj USPAT; rh adj double adj layer\$) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	-	4	(nitride adj semiconductor) and (double		2004/10/29 21:30
DERWENT; IBM_TDB USPAT; rh adj double adj layer\$) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;				Į.	
- 0 (nitride adj semiconductor) and (ir adj USPAT; US-PGPUB; EPO; JPO; DERWENT;			or rhodium))	· .	
- 0 (nitride adj semiconductor) and (ir adj USPĀT; rh adj double adj layer\$) US-PGPUB; EPO; JPO; DERWENT;		·			
rh adj double adj layer\$) US-PGPUB; EPO; JPO; DERWENT;	_		(nitride add semiconductor) and (is add		2004/10/20 21:21
EPO; JPO; DERWENT;					2004/10/29 21:31
DERWENT;				l :	
				IBM TDB	

-	0	(nitride adj semiconductor) and (ir adj		2004/10/29 21:32
		rh adj multi adj layer\$)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(nitride adj semiconductor) and (ir adj		2004/10/29 21:33
		rh adj multiple adj layer\$)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/10/00 01 00
-	0	(nitride adj semiconductor) and (ir adj rh adj dual adj layer\$)	USPAT; US-PGPUB;	2004/10/29 21:33
		III adj dual adj layely/	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(USPAT;	2004/10/29 21:33
		rh adj two adj layer\$)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	0	(nitride adj semiconductor) and (ir adj		2004/10/29 21:34
	J	rh adj multilayer)	US-PGPUB;	2001/10/25 21.54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	[(======		2004/10/29 21:34
		rh) with multilayer)	US-PGPUB;	
			EPO; JPO; DERWENT;	,
:			IBM TDB	
-	О	(nitride adj semiconductor) and ((ir adj		2004/10/29 21:34
		rh) same multilayer)	US-PGPUB;	
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/10/00 01 05
-	0	(nitride adj semiconductor) and ((ir adj rh) and multilayer)	· · ·	2004/10/29 21:35
1 - 1		in, and mulcilayer,	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	' ',		2004/10/29 21:35
		rh) and multilayer)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	97	(nitride) and ((ir adj rh) and multilayer)		2004/10/29 21:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/10/00 55
-	11	, , , , , , , , , , , , , , , , , , , ,		2004/10/29 21:40
		multilayer)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(nitride) and ((ir adj rh) with (two adj		2004/10/29 21:41
		layered))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	2	5990500.pn.	IBM_TDB USPAT;	2004/10/29 21:42
	2		US-PGPUB;	2003/10/23 21.42
·			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	5990500.pn. and ir and rh		2004/10/29 21:47
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
·		<u> </u>	_ _	

-	862	stacked adj electrode	USPAT;	2004/10/29 21:47
			US-PGPUB;	İ
			EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	
-	9	(stacked adj electrode) and nitride and	USPAT;	2004/10/29 21:52
		(ir with rh)	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	83	(electrode adj stack) and nitride and (ir	USPAT;	2004/10/29 22:03
	63			2004/10/29 22.03
		with rh)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	·
-	18	(USPAT;	2004/10/29 22:07
		(ir with rh)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3	(electrode) and nitride and (ir near	USPAT;	2004/10/29 22:09
		formed near rh)	US-PGPUB;	
ł		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	16	(electrode) and nitride and (ir adj rh adj	USPAT;	2004/10/29 22:14
	10	alloy)	US-PGPUB;	2004/10/29 22.14
		alloy	EPO; JPO;	
		,		1
			DERWENT;	l i
	9	/	IBM_TDB	0004/10/00 00 15
-	٩	(compound day crocerode, and mreride and	USPAT;	2004/10/29 22:15
		(ir near rh)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	((USPAT;	2004/10/29 23:32
		and nitride	US-PGPUB;] , "
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3	((rh with ir) with electrode with anneal\$)	USPAT;	2004/10/29 23:34
		and nitride	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	11	((rh with ir) with electrode with	USPAT;	2004/10/31 09:30
]		temperature) and nitride	US-PGPUB;	====, ==, == = = = = = = = = = = = = =
1			EPO; JPO;	
	i		DERWENT;	
			IBM TDB	
L		1	TOM TOD	